

1617AB35

35 Watts, 25 Volts, Class AB Satcom 1600 - 1700 MHz

GENERAL DESCRIPTION

The 1617AB35 is a COMMON EMITTER transistor capable of providing 35 Watts of Class AB, RF output power over the band 1600 - 1700 MHz. This transistor is specifically designed for **SATCOM COMMUNICATIONS** amplifier applications. It includes Input prematching and utilizes Gold metalization and EMITTER BALLASTING to provide high reliability and supreme ruggedness. .

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C 120 Watts

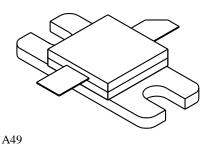
Maximum Voltage and Current

BVcesCollector to Emitter Voltage60 VoltsLVceoCollector to Emitter Voltage27 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current14.0 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 150^{\circ}\text{C}$ Operating Junction Temperature $+230^{\circ}\text{C}$

CASE OUTLINE 55AR, STYLE 2 COMMON EMITTER



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c VSWR	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance 3rd Order IMD	F=1700 MHz Vce = 25 Volts Icq = 250 mAmps As Above As Above As Above	35 9.0	10.0 50	4.5 3:1 -30	Watt Watt dB %

BVces LVceo	Collector to Emitter Breakdown Collector to Emitter Breakdown	Ic = 50 mA Ic = 50 mA	60 27			Volts Volts
BVebo	Emitter to Base Breakdown	Ic = 30 mA $Ie = 10 mA$	3.5			Volts
Ices	Collector Leakage Current	Vce = 27 Volts	3.3		10	mA
h _{FE}	DC - Current Gain	Vcc = 27 Voits Vce = 5 V, Ic = 0.7 A	20		100	ША
Cob	Output Capacitance	F = 1 MHz, Vcb = 28 V	20	36	100	pF
θ jc	Thermal Resistance	$Tc = 25^{\circ}C$			1.6	°C/W

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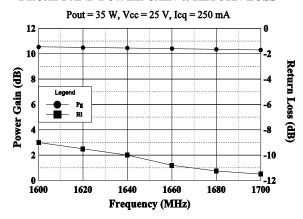
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CHz TECHNOLOCY

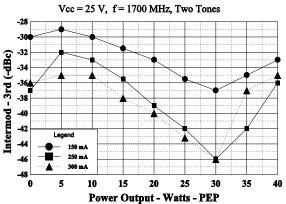
Typical Performance

1617AB35

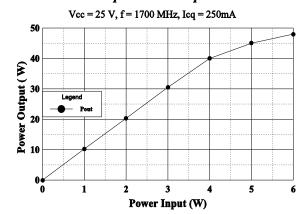
BROADBAND POWER GAIN & RETURN LOSS



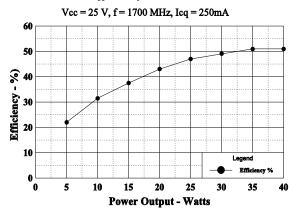
THIRD ORDER IMD vs POWER OUTPUT



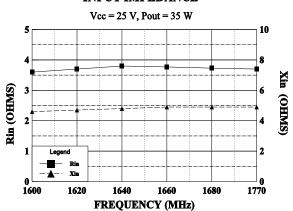
Power Output vs Power Input - PEP



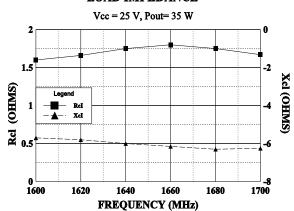
Collector Efficiency vs Power Out - PEP



INPUT IMPEDANCE

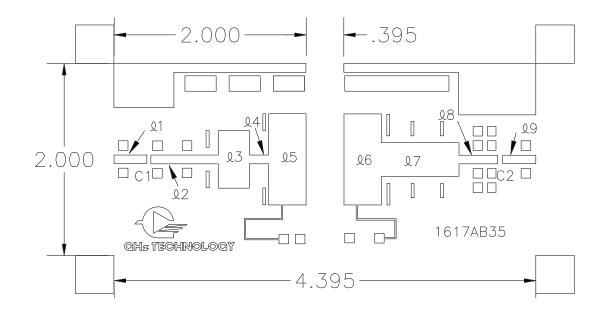


LOAD IMPEDANCE





	REVISIONS					
ZONE	REV	DESCRIPTION	DATE	APPROVED		



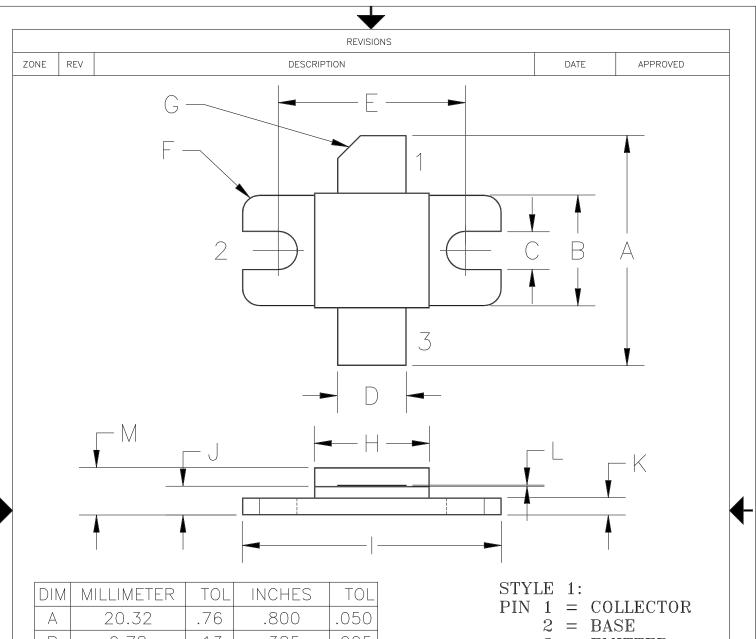
C1,C2=100pf ATC 1/32" PTFE glass Er=2.5

l NO.	X DIM	Y DIM
1	.340	.089
2	.700	.089
3	.325	.600
4	.200	.089
5	.390	.950
6	.390	.950
7	.810	.350
8	.405	.089
9	.346	.089

DATE: 6 FEB 96



cage 0PJR2	DWG NO.	1617AB35		REV _
	SCALE	1/1	SHEET	



DIM	MILLIMETER	TOL	INCHES	TOL
Α	20.32	.76	.800	.050
В	9.78	.13	.385	.005
С	3.30	.13	.130	.005
D	6.10	.13	.240	.005
Е	16.51	.13	.650	.005
F	1.52 R	.13	.060 R	.005
G	45°	5°	45°	5°
Н	10.16 SQ	.13	.400 SQ	.005
	22.86	.13	.900	.005
J	2.54	.13	.100	.005
K	1.52	.13	.060	.005
L	.102	.02	.004	.001
М	4.19	.13	.165	.005

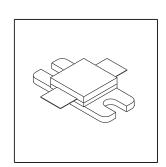
3 = EMITTER

STYLE 2:

PIN 1 = COLLECTOR

2 = EMITTER

3 = BASE





GHz TECHNOLOGY

cage 0PJR2	DWG NO.	55AR		REV A
	SCALE	3/1	SHEET	